

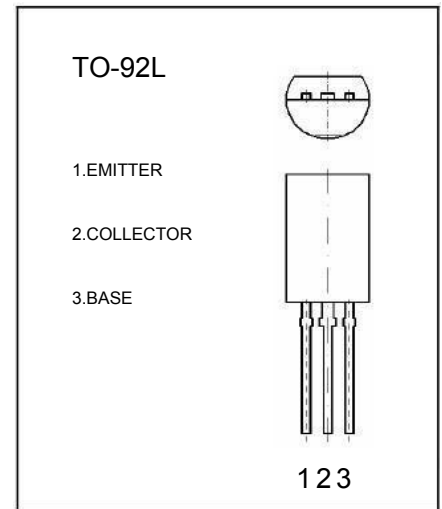


TO-92L Plastic-Encapsulate Transistors

C2271 TRANSISTOR (NPN)

FEATURES

Low collector to emitter saturation voltage $V_{CE(sat)}$.



MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter		Units
V_{CBO}	Collector-Base Voltage	300	V
V_{CEO}	Collector-Emitter Voltage	300	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current – Continuous	0.1	A
P_C	Collector Power Dissipation	0.9	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector cut-off current	I_{CBO}	$V_{CB}=200\text{V}, I_E=0$			1.0	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=6\text{V}, I_C=0$			1.0	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=10\text{V}, I_C=10\text{mA}$	40		200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=20\text{mA}, I_B=2\text{mA}$			0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=20\text{mA}, I_B=2\text{mA}$			1.0	V
Transition frequency	f_T	$V_{CE}=30\text{V}, I_C=10\text{mA}$	50			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	C	D	E
Range	40-80	60-120	100-200